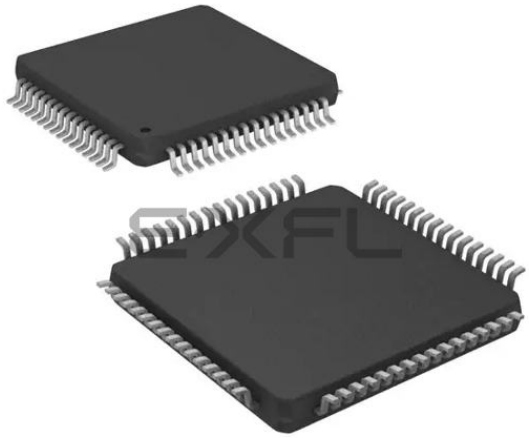
Microchip Technology - ATXMEGA32C3-AU Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	AVR
Core Size	8/16-Bit
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	50
Program Memory Size	32KB (16K x 16)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/atxmega32c3-au

7. Memories

7.1 Features

- Flash program memory
  - One linear address space
  - In-system programmable
  - Self-programming and boot loader support
  - Application section for application code
  - Application table section for application code or data storage
  - Boot section for application code or boot loader code
  - Separate read/write protection lock bits for all sections
  - Built in fast CRC check of a selectable flash program memory section
- Data memory
  - One linear address space
  - Single-cycle access from CPU
  - SRAM
  - EEPROM
    - Byte and page accessible
    - Optional memory mapping for direct load and store
  - I/O memory
    - Configuration and status registers for all peripherals and modules
    - Four bit-accessible general purpose registers for global variables or flags
  - Separate buses for SRAM, EEPROM and I/O memory
    - Simultaneous bus access for CPU
- Production signature row memory for factory programmed data
  - ID for each microcontroller device type
  - Serial number for each device
  - Calibration bytes for factory calibrated peripherals
- User signature row
  - One flash page in size
  - Can be read and written from software
  - Content is kept after chip erase

7.2 Overview

The Atmel AVR architecture has two main memory spaces, the program memory and the data memory. Executable code can reside only in the program memory, while data can be stored in the program memory and the data memory. The data memory includes the internal SRAM, and EEPROM for nonvolatile data storage. All memory spaces are linear and require no memory bank switching. Nonvolatile memory (NVM) spaces can be locked for further write and read/write operations. This prevents unrestricted access to the application software.

A separate memory section contains the fuse bytes. These are used for configuring important system functions, and can only be written by an external programmer.

The available memory size configurations are shown in “Pinout/Block Diagram” on page 4. In addition, each device has a Flash memory signature row for calibration data, device identification, serial number etc.

7.3 Flash Program Memory

The Atmel AVR XMEGA devices contain on-chip, in-system reprogrammable flash memory for program storage. The flash memory can be accessed for read and write from an external programmer through the PDI or from application software running in the device.

23. USART

23.1 Features

- Three identical USART peripherals
- Full-duplex operation
- Asynchronous or synchronous operation
  - Synchronous clock rates up to 1/2 of the device clock frequency
  - Asynchronous clock rates up to 1/8 of the device clock frequency
- Supports serial frames with 5, 6, 7, 8, or 9 data bits and 1 or 2 stop bits
- Fractional baud rate generator
  - Can generate desired baud rate from any system clock frequency
  - No need for external oscillator with certain frequencies
- Built-in error detection and correction schemes
  - Odd or even parity generation and parity check
  - Data overrun and framing error detection
  - Noise filtering includes false start bit detection and digital low-pass filter
- Separate interrupts for
  - Transmit complete
  - Transmit data register empty
  - Receive complete
- Multiprocessor communication mode
  - Addressing scheme to address a specific devices on a multidevice bus
  - Enable unaddressed devices to automatically ignore all frames
- Master SPI mode
  - Double buffered operation
  - Operation up to 1/2 of the peripheral clock frequency
- IRCOM module for IrDA compliant pulse modulation/demodulation

23.2 Overview

The universal synchronous and asynchronous serial receiver and transmitter (USART) is a fast and flexible serial communication module. The USART supports full-duplex communication and asynchronous and synchronous operation. The USART can be configured to operate in SPI master mode and used for SPI communication.

Communication is frame based, and the frame format can be customized to support a wide range of standards. The USART is buffered in both directions, enabling continued data transmission without any delay between frames. Separate interrupts for receive and transmit complete enable fully interrupt driven communication. Frame error and buffer overflow are detected in hardware and indicated with separate status flags. Even or odd parity generation and parity check can also be enabled.

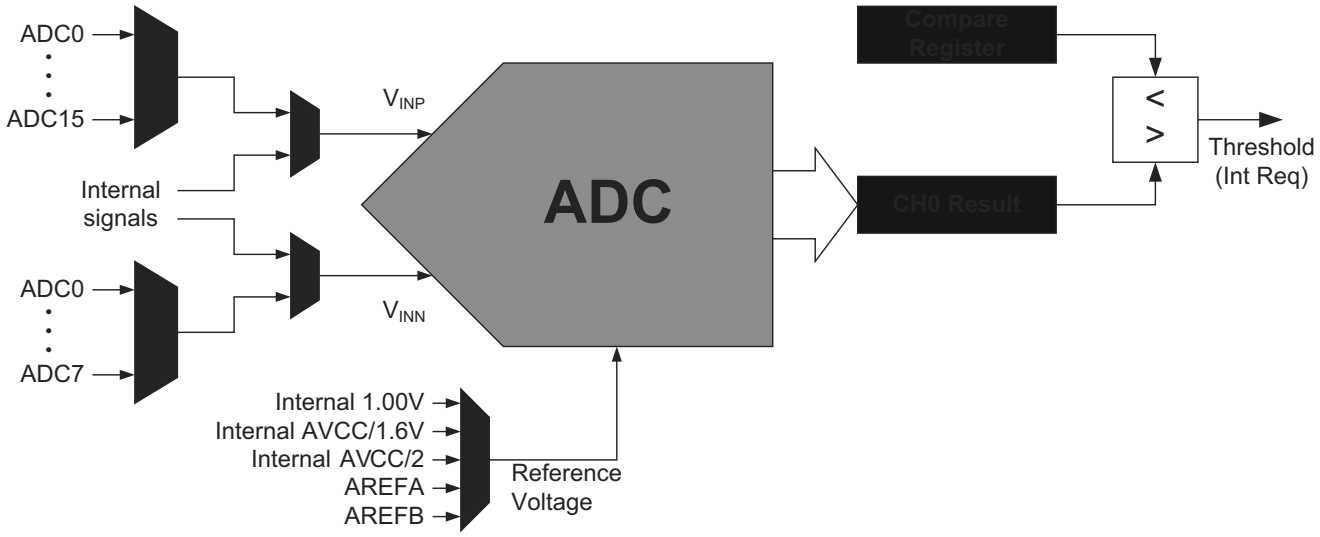
The clock generator includes a fractional baud rate generator that is able to generate a wide range of USART baud rates from any system clock frequencies. This removes the need to use an external crystal oscillator with a specific frequency to achieve a required baud rate. It also supports external clock input in synchronous slave operation.

When the USART is set in master SPI mode, all USART-specific logic is disabled, leaving the transmit and receive buffers, shift registers, and baud rate generator enabled. Pin control and interrupt generation are identical in both modes. The registers are used in both modes, but their functionality differs for some control settings.

An IRCOM module can be enabled for one USART to support IrDA 1.4 physical compliant pulse modulation and demodulation for baud rates up to 115.2kbps.

PORTC, PORTD, and PORTE each has one USART. Notation of these peripherals are USARTC0, USARTD0, and USARTE0, respectively.

Figure 26-1. ADC Overview



The ADC may be configured for 8- or 12-bit result, reducing the minimum conversion time (propagation delay) from 3.35µs for 12-bit to 2.3µs for 8-bit result.

ADC conversion results are provided left- or right adjusted with optional ‘1’ or ‘0’ padding. This eases calculation when the result is represented as a signed integer (signed 16-bit number).

PORTA has one ADC. Notation of this peripheral is ADCA.

Table 29-5. Port E - Alternate Functions

PORT E	PIN #	INTERRUPT	TCE0	USARTE0	TOSC	TWIE	CLOCKOUT	EVENTOUT
PE0	36	SYNC	OC0A			SDA		
PE1	37	SYNC	OC0B	XCK0		SCL		
PE2	38	SYNC/ASYNC	OC0C	RXD0				
PE3	39	SYNC	OC0D	TXD0				
PE4	40	SYNC						
PE5	41	SYNC						
PE6	42	SYNC			TOSC2			
PE7	43	SYNC			TOSC1		Clk_{PER}	EVOUT
GND	44							
VCC	45							

Table 29-6. Port F - Alternate Functions

PORT F	PIN #	INTERRUPT	TCF0
PF0	46	SYNC	OC0A
PF1	47	SYNC	OC0B
PF2	48	SYNC/ASYNC	OC0C
PF3	49	SYNC	OC0D
PF4	50	SYNC	
PF5	51	SYNC	
PF6	54	SYNC	
PF7	55	SYNC	
GND	52		
VCC	53		

Table 29-7. Port R - Alternate Functions

PORT R	PIN #	INTERRUPT	PDI	XTAL
PDI	56		PDI_DATA	
$\overline{\text{RESET}}$	57		PDI_CLOCK	
PRO	58	SYNC		XTAL2
PR1	59	SYNC		XTAL1

Table 33-25. External Clock with Prescaler (1) for System Clock

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
$1/t_{CK}$	Clock Frequency (2)	V_{CC} = 1.6 - 1.8V	0		90	MHz
		V_{CC} = 2.7 - 3.6V	0		142	
t_{CK}	Clock Period	V_{CC} = 1.6 - 1.8V	11			ns
		V_{CC} = 2.7 - 3.6V	7			
t_{CH}	Clock High Time	V_{CC} = 1.6 - 1.8V	4.5			
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CL}	Clock Low Time	V_{CC} = 1.6 - 1.8V	4.5			
		V_{CC} = 2.7 - 3.6V	2.4			
t_{CR}	Rise Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	
		V_{CC} = 2.7 - 3.6V			1.0	
t_{CF}	Fall Time (for maximum frequency)	V_{CC} = 1.6 - 1.8V			1.5	
		V_{CC} = 2.7 - 3.6V			1.0	
Δt_{CK}	Change in period from one clock cycle to the next				10	%

Notes: 1. System Clock Prescalers must be set so that maximum CPU clock frequency for device is not exceeded.
2. The maximum frequency vs. supply voltage is linear between 1.6V and 2.7V, and the same applies for all other parameters with supply voltage conditions.

33.1.13.7 External 16MHz Crystal Oscillator and XOSC Characteristics

Table 33-26. External 16MHz Crystal oOcillator and XOSC Characteristics

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Cycle to cycle jitter	XOSCPWR=0	FRQRANGE=0		0		ns
			FRQRANGE=1, 2, or 3		0		
		XOSCPWR=1			0		
	Long term jitter	XOSCPWR=0	FRQRANGE=0		0		
			FRQRANGE=1, 2, or 3		0		
		XOSCPWR=1			0		
	Frequency error	XOSCPWR=0	FRQRANGE=0		0.03		%
			FRQRANGE=1		0.03		
			FRQRANGE=2 or 3		0.03		
		XOSCPWR=1			0.003		
	Duty cycle	XOSCPWR=0	FRQRANGE=0		50		
			FRQRANGE=1		50		
			FRQRANGE=2 or 3		50		
		XOSCPWR=1			50		

33.2.3 Current Consumption

Table 33-33. Current Consumption for Active Mode and Sleep Modes

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
I_{CC}	Active power consumption(1)	32kHz, Ext. Clk	V_{CC} = 1.8V		50		µA
			V_{CC} = 3.0V		130		
		1MHz, Ext. Clk	V_{CC} = 1.8V		215		
			V_{CC} = 3.0V		475		
		2MHz, Ext. Clk	V_{CC} = 1.8V		445	600	
			V_{CC} = 3.0V		0.95	1.5	mA
		32MHz, Ext. Clk			7.8	12	
	Idle power consumption(2)	32kHz, Ext. Clk	V_{CC} = 1.8V		2.8		µA
			V_{CC} = 3.0V		3.0		
		1MHz, Ext. Clk	V_{CC} = 1.8V		46		
			V_{CC} = 3.0V		92		
		2MHz, Ext. Clk	V_{CC} = 1.8V		93	225	
			V_{CC} = 3.0V		184	350	
		32MHz, Ext. Clk			2.9	5.0	mA
	Power-down power consumption	T = 25°C	V_{CC} = 3.0V		0.07	1.0	µA
		T = 85°C			1.3	5.0	
		T = 105°C			4.0	8.0	
		WDT and sampled BOD enabled, T = 25°C	V_{CC} = 3.0V		1.4	2.0	
		WDT and sampled BOD enabled, T = 85°C			2.6	6.0	
		WDT and sampled BOD enabled, T = 105°C			5.0	10	
	Power-save power consumption(3)	RTC from ULP clock, WDT and sampled BOD enabled, T = 25°C	V_{CC} = 1.8V		1.7		
			V_{CC} = 3.0V		1.8		
		RTC from 1.024kHz low power 32.768kHz TOSC, T = 25°C	V_{CC} = 1.8V		0.7	2.0	
			V_{CC} = 3.0V		0.8	2.0	
		RTC from low power 32.768kHz TOSC, T = 25°C	V_{CC} = 1.8V		0.9	3.0	
			V_{CC} = 3.0V		1.2	3.0	
	Reset power consumption	Current through $\overline{\text{RESET}}$ pin substracted	V_{CC} = 3.0V		120		

Notes:
1. All Power Reduction Registers set including FPRM and EPRM.
2. All Power Reduction Registers set without FPRM and EPRM.
3. Maximum limits are based on characterization, and not tested in production.

33.2.11 Power-on Reset Characteristics

Table 33-45. Power-on Reset Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{POT-} (1)	POR threshold voltage falling V_{CC}	V_{CC} falls faster than 1V/ms	0.4	1.0		V
		V_{CC} falls at 1V/ms or slower	0.8	1.3		
V_{POT+}	POR threshold voltage rising V_{CC}			1.3	1.59	

Note: 1. V_{POT-} values are only valid when BOD is disabled. When BOD is enabled $V_{POT-} = V_{POT+}$.

33.2.12 Flash and EEPROM Memory Characteristics

Table 33-46. Endurance and Data Retention

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Flash	Write/Erase cycles	25°C	10K			Cycle
			85°C	10K			
			105°C	2K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			
	EEPROM	Write/Erase cycles	25°C	100K			Cycle
			85°C	100K			
			105°C	30K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			

Table 33-47. Programming Time

Symbol	Parameter	Condition	Min.	Typ.(1)	Max.	Units
	Chip erase(2)	64KB Flash, EEPROM		55		ms
	Application erase	Section erase		6		
	Flash	Page erase		4		
		Page write		4		
		Atomic page erase and write		8		
	EEPROM	Page erase		4		
		Page write		4		
		Atomic page erase and write		8		

Notes: 1. Programming is timed from the 2MHz internal oscillator.
2. EEPROM is not erased if the EESAVE fuse is programmed.

33.4.11 Power-on Reset Characteristics

Table 33-103. Power-on Reset Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
V_{POT-} (1)	POR threshold voltage falling V_{CC}	V_{CC} falls faster than 1V/ms	0.4	1.0		V
		V_{CC} falls at 1V/ms or slower	0.8	1.3		
V_{POT+}	POR threshold voltage rising V_{CC}			1.3	1.59	

Note: 1. V_{POT-} values are only valid when BOD is disabled. When BOD is enabled $V_{POT-} = V_{POT+}$.

33.4.12 Flash and EEPROM Memory Characteristics

Table 33-104. Endurance and Data Retention

Symbol	Parameter	Condition		Min.	Typ.	Max.	Units
	Flash	Write/Erase cycles	25°C	10K			Cycle
			85°C	10K			
			105°C	2K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			
	EEPROM	Write/Erase cycles	25°C	100K			Cycle
			85°C	100K			
			105°C	30K			
		Data retention	25°C	100			Year
			85°C	25			
			105°C	10			

Table 33-105. Programming Time

Symbol	Parameter	Condition	Min.	Typ. (1)	Max.	Units
	Chip erase(2)	192KB Flash, EEPROM		90		ms
	Application erase	Section erase		6		
	Flash	Page erase		4		
		Page write		4		
		Atomic page erase and write		8		
	EEPROM	Page erase		4		
		Page write		4		
		Atomic page erase and write		8		

Notes: 1. Programming is timed from the 2MHz internal oscillator.
2. EEPROM is not erased if the EESAVE fuse is programmed.

Figure 34-35. DNL Error vs. Sample Rate

T = 25°C, V_{CC} = 3.6V, V_{REF} = 3.0V external

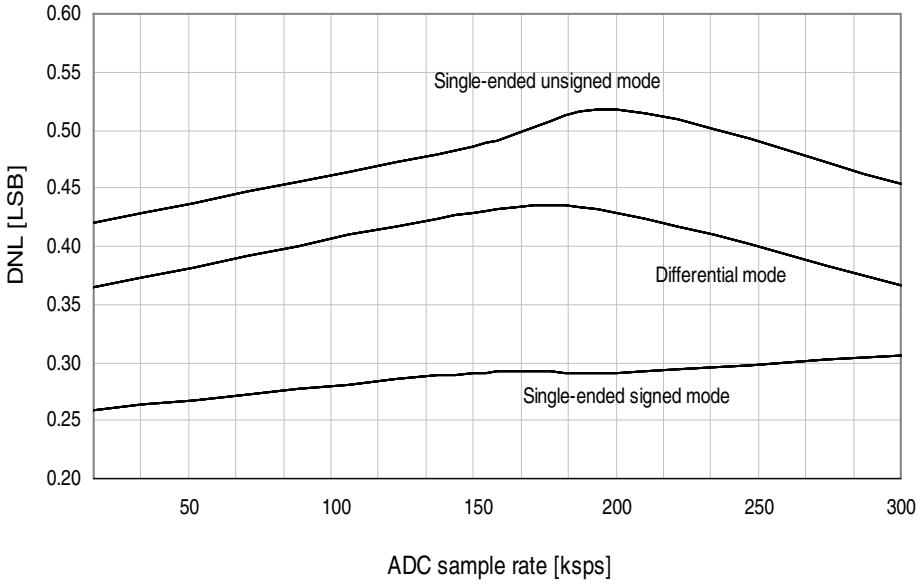


Figure 34-36. DNL Error vs. Input Code

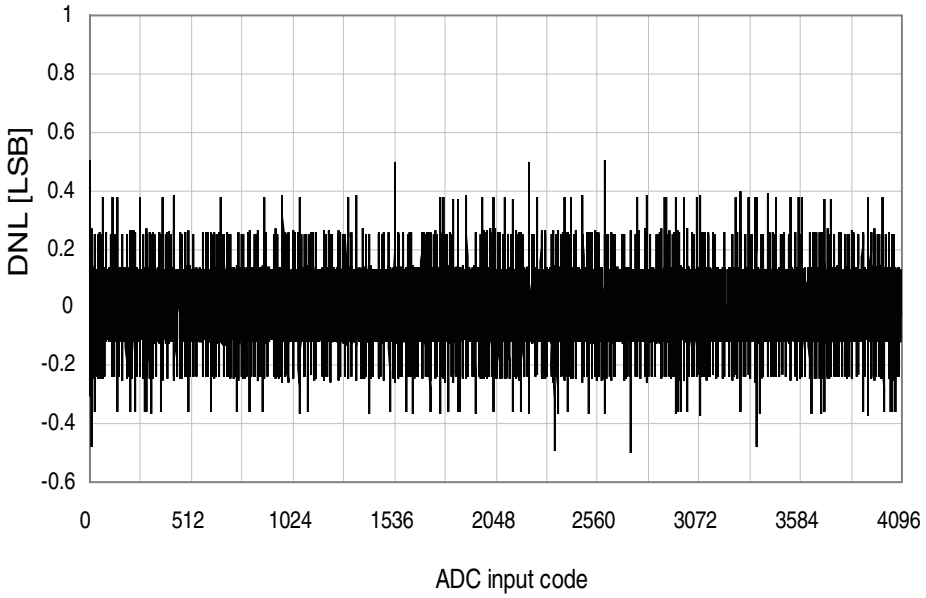


Figure 34-39. Offset Error vs. V_{REF}

T = 25°C, V_{CC} = 3.6V, ADC sample rate = 300ksps

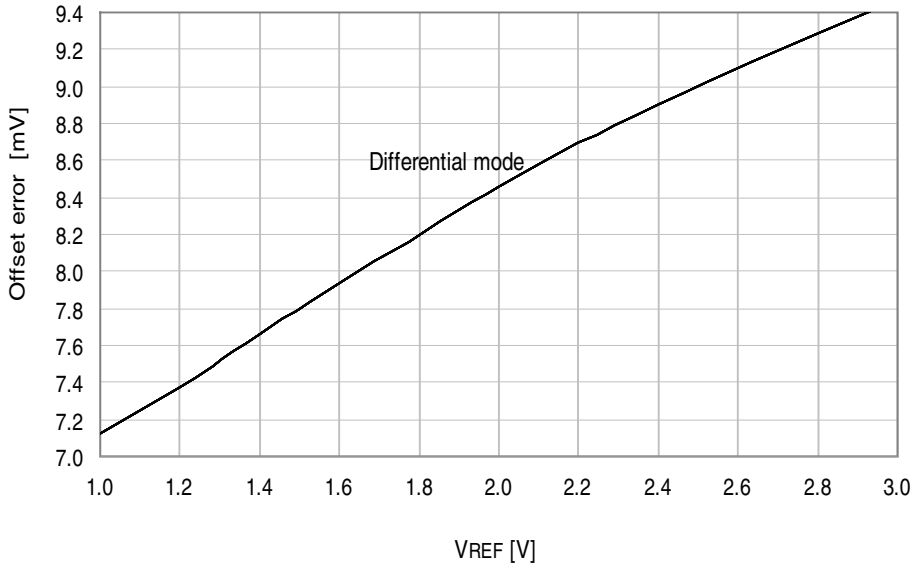


Figure 34-40. Gain Error vs. Temperature

V_{CC} = 3.0V, V_{REF} = external 2.0V

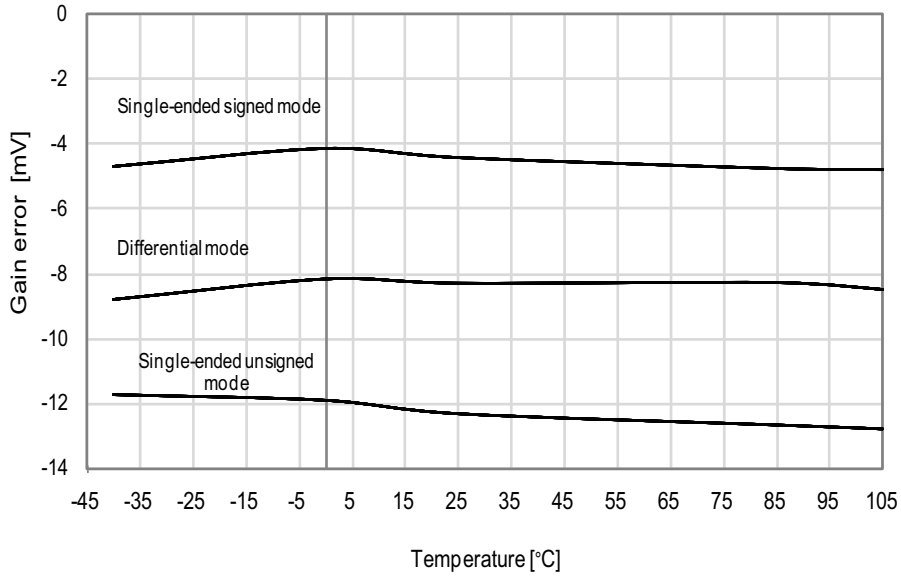
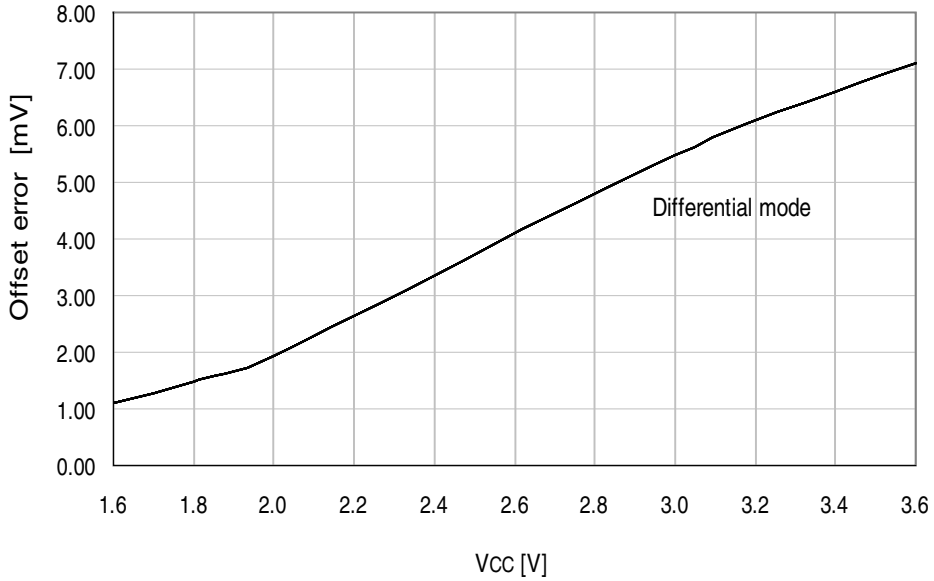


Figure 34-41. Offset Error vs. V_{CC}

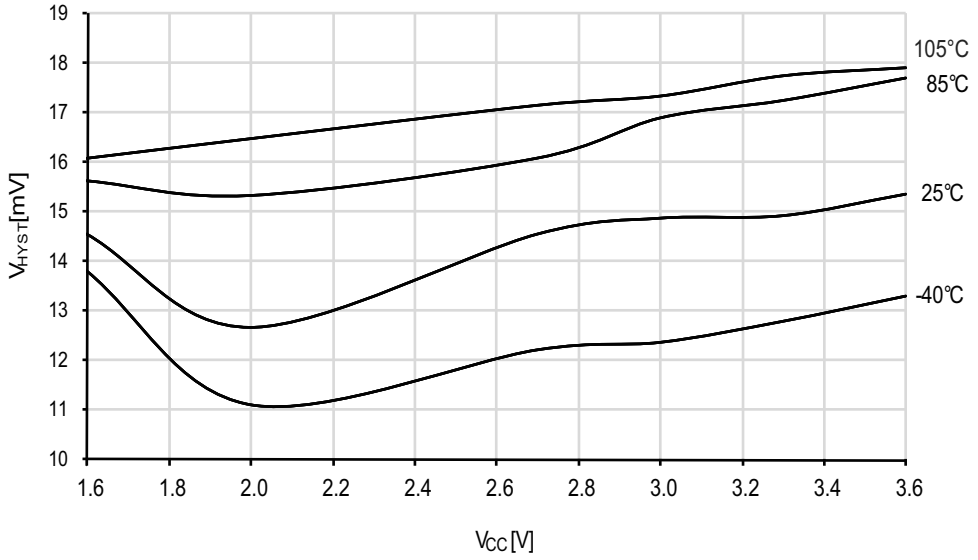
T = 25°C, V_{REF} = external 1.0V, ADC sample rate = 300ksps



34.1.4 Analog Comparator Characteristics

Figure 34-42. Analog Comparator Hysteresis vs. V_{CC}

Small hysteresis



34.3 Atmel ATxmega128C3

34.3.1 Current Consumption

34.3.1.1 Active Mode Supply Current

Figure 34-143. Active Supply Current vs. Frequency

f_{SYS} = 0 - 1MHz external clock, T = 25°C

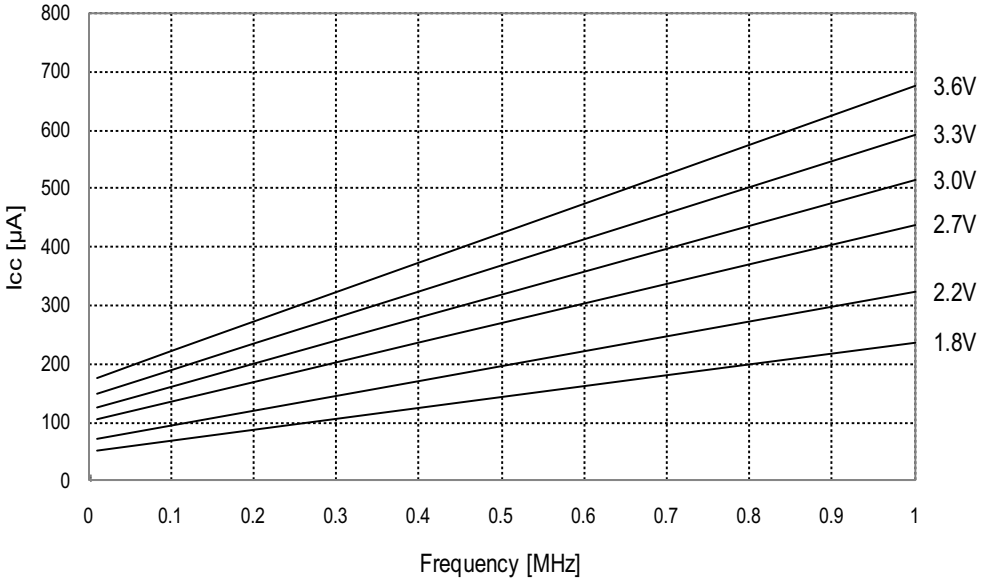


Figure 34-144. Active Supply Current vs. Frequency

f_{SYS} = 1 - 32MHz external clock, T = 25°C

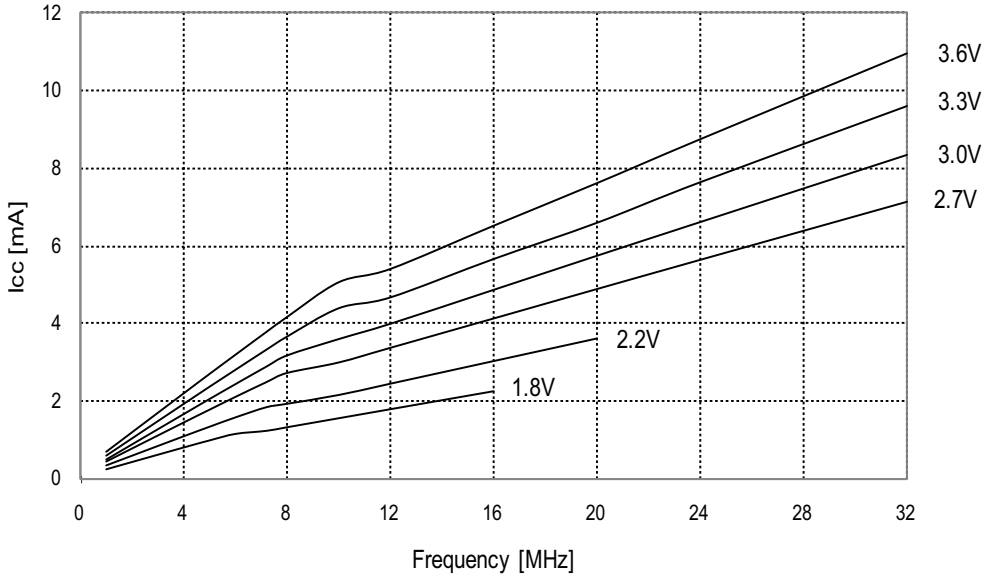


Figure 34-151. Idle Mode Supply Current vs. Frequency

f_{SYS} = 1 - 32MHz external clock, T = 25°C

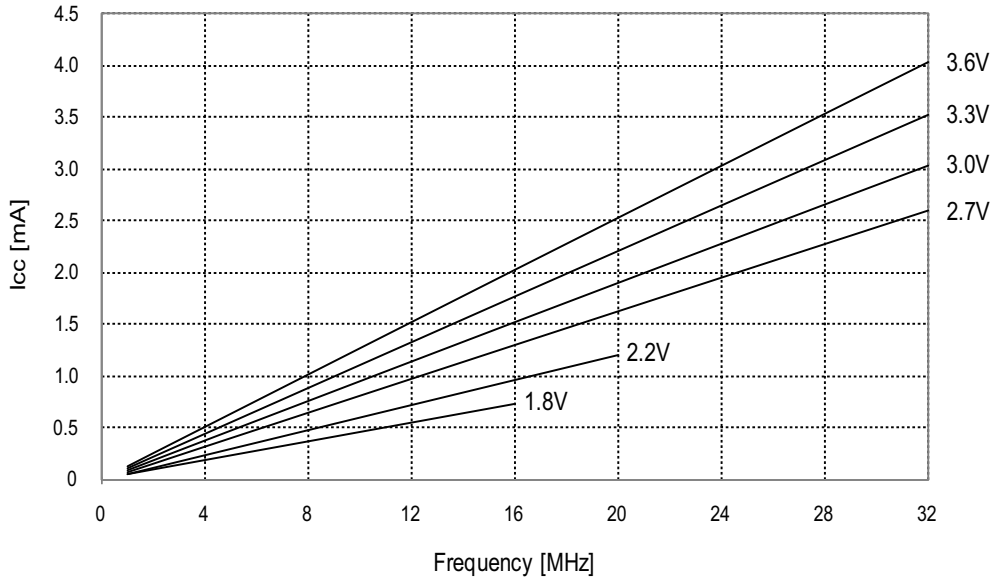


Figure 34-152. Idle Mode Supply Current vs. V_{CC}

f_{SYS} = 32.768kHz internal oscillator

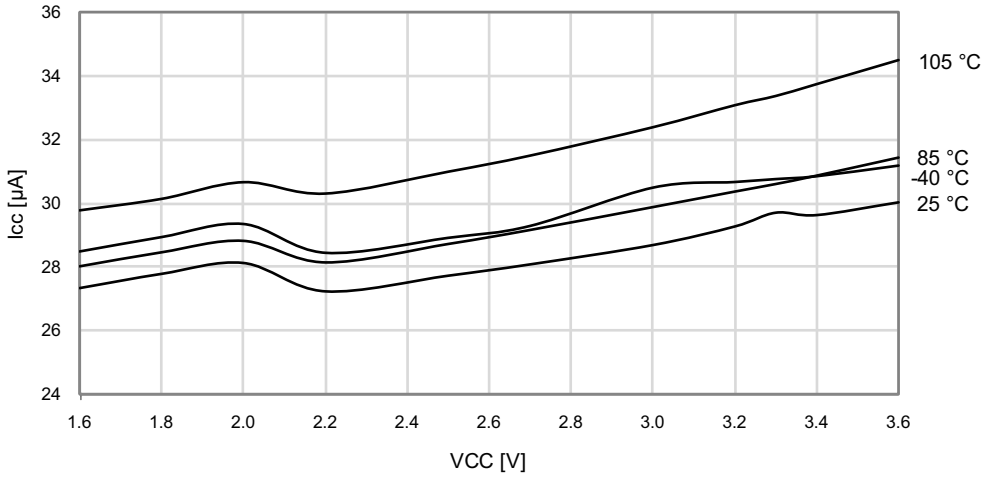


Figure 34-155. Idle Mode Supply Current vs. V_{CC}

f_{SYS} = 32MHz internal oscillator prescaled to 8MHz

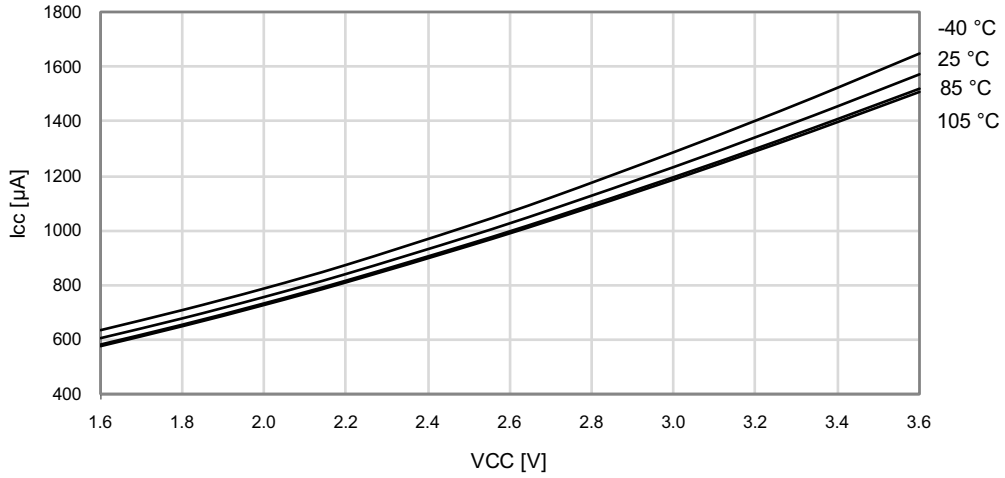


Figure 34-156. Idle Mode Current vs. V_{CC}

f_{SYS} = 32MHz internal oscillator

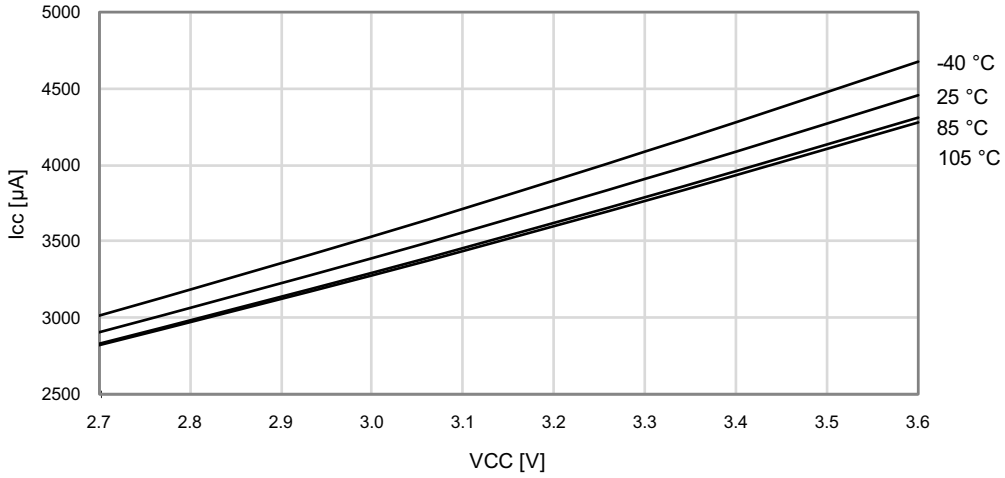


Figure 34-161. I/O Pin Pull-up Resistor Current vs. Input Voltage

V_{CC} = 3.0V

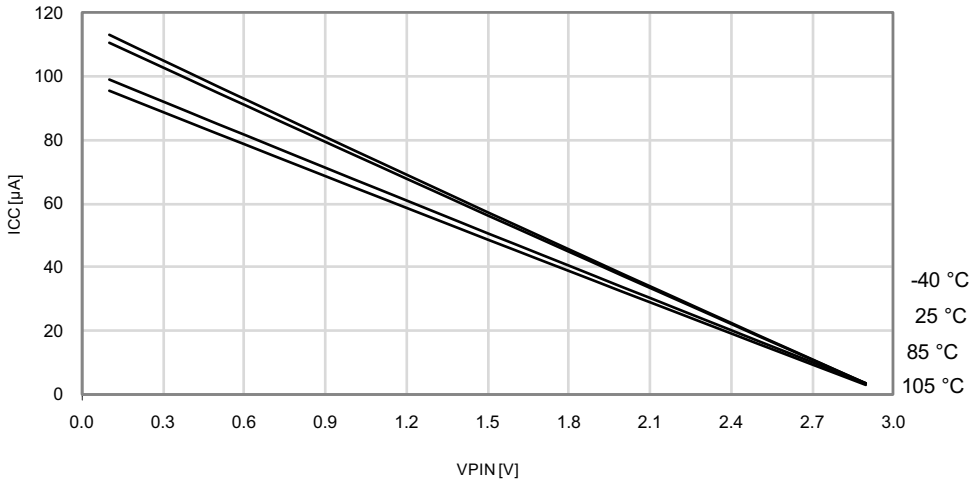


Figure 34-162. I/O Pin Pull-up Resistor Current vs. Input Voltage

V_{CC} = 3.3V

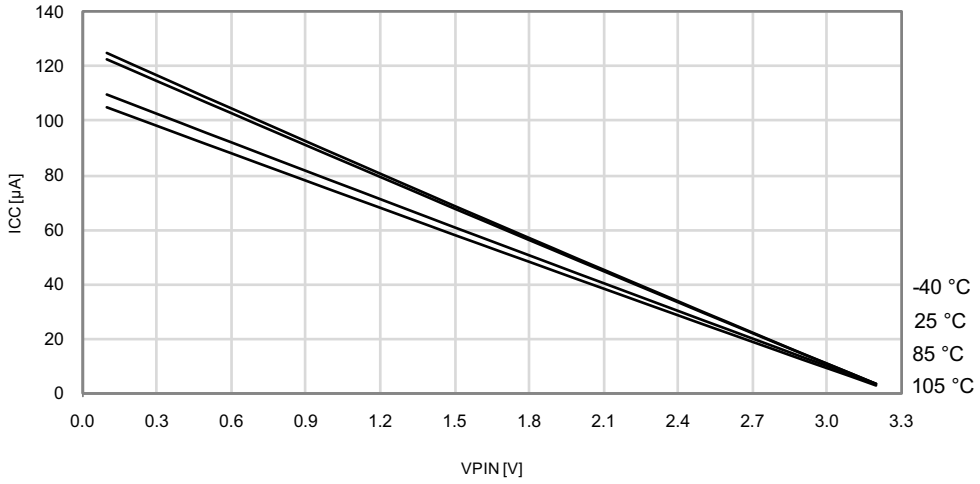


Figure 34-215. Active Mode Supply Current vs. V_{CC}

f_{SYS} = 32.768kHz internal oscillator

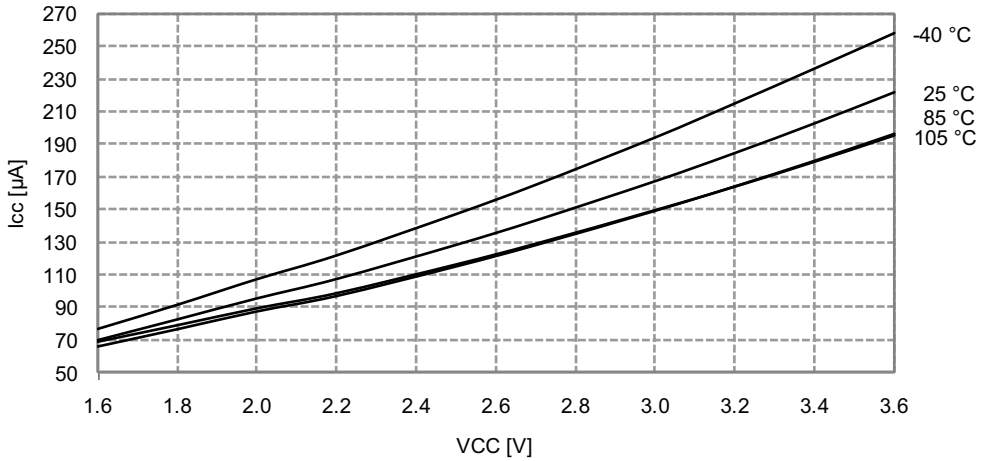


Figure 34-216. Active Mode Supply Current vs. V_{CC}

f_{SYS} = 1MHz external clock

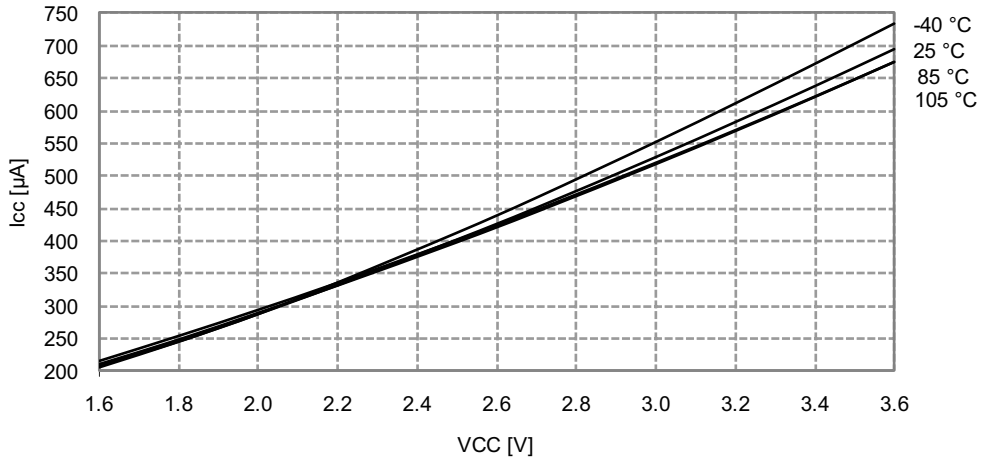


Figure 34-231. I/O Pin Pull-up Resistor Current vs. Input Voltage

V_{CC} = 3.0V

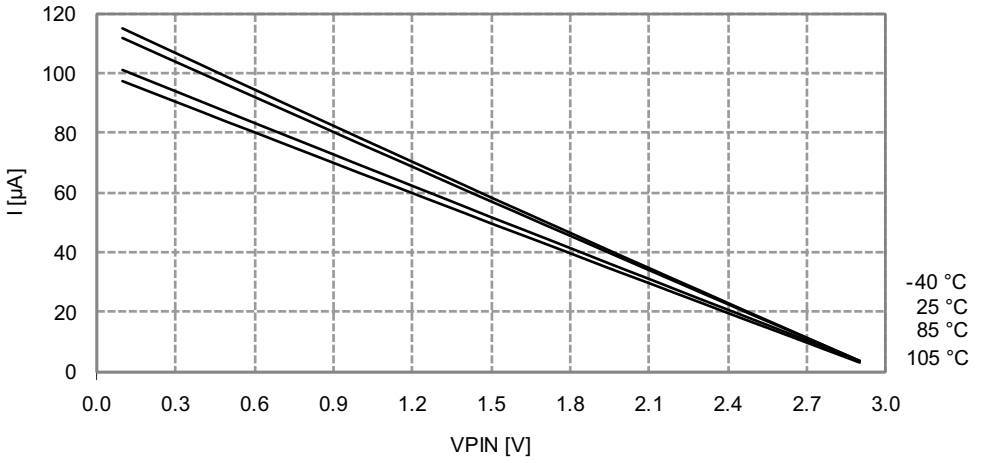


Figure 34-232. I/O Pin Pull-up Resistor Current vs. Input Voltage

V_{CC} = 3.3V

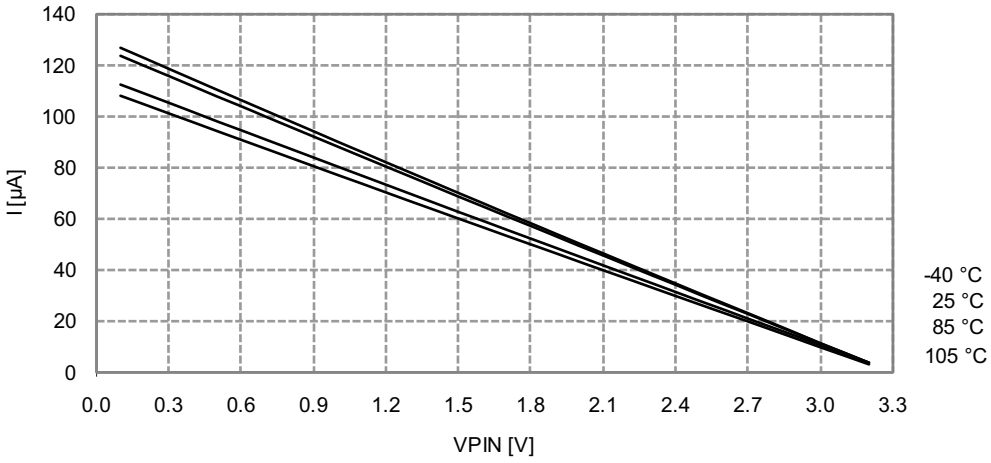


Figure 34-291. Idle Mode Supply Current vs. Frequency

f_{SYS} = 1 - 32MHz external clock, T = 25°C

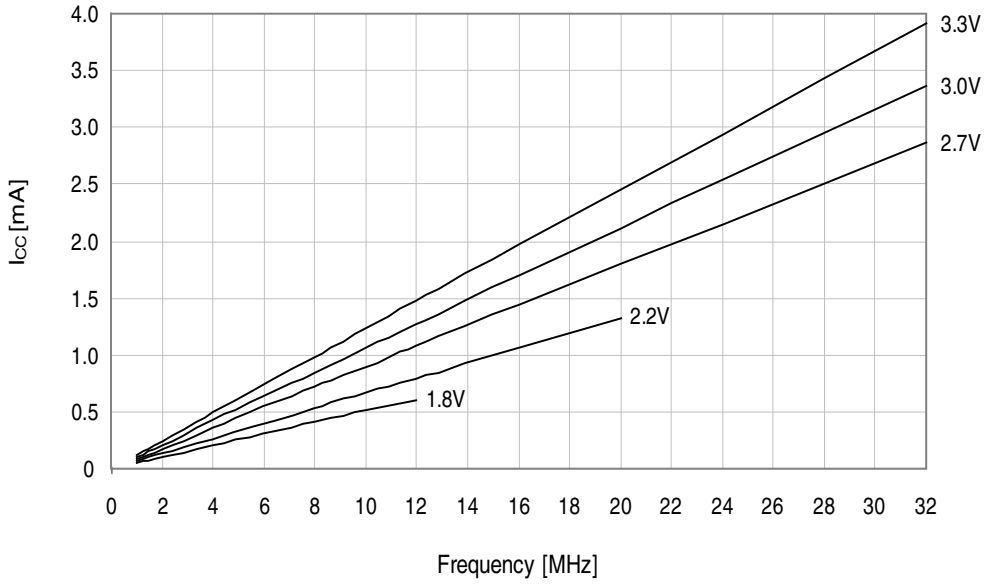


Figure 34-292. Idle Mode Supply Current vs. V_{CC}

f_{SYS} = 32.768kHz internal oscillator

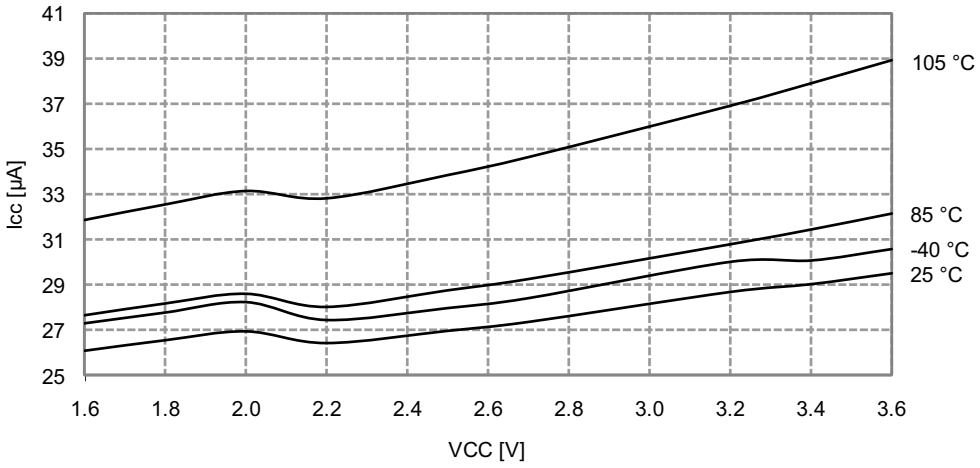
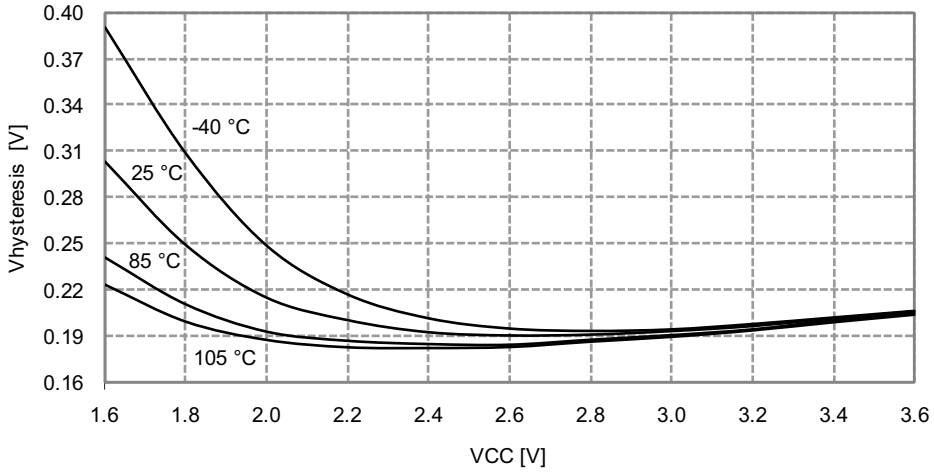


Figure 34-311. I/O Pin Input Hysteresis vs. V_{CC}



34.5.3 ADC Characteristics

Figure 34-312. INL Error vs. External V_{REF}

T = 25°C, V_{CC} = 3.6V, external reference

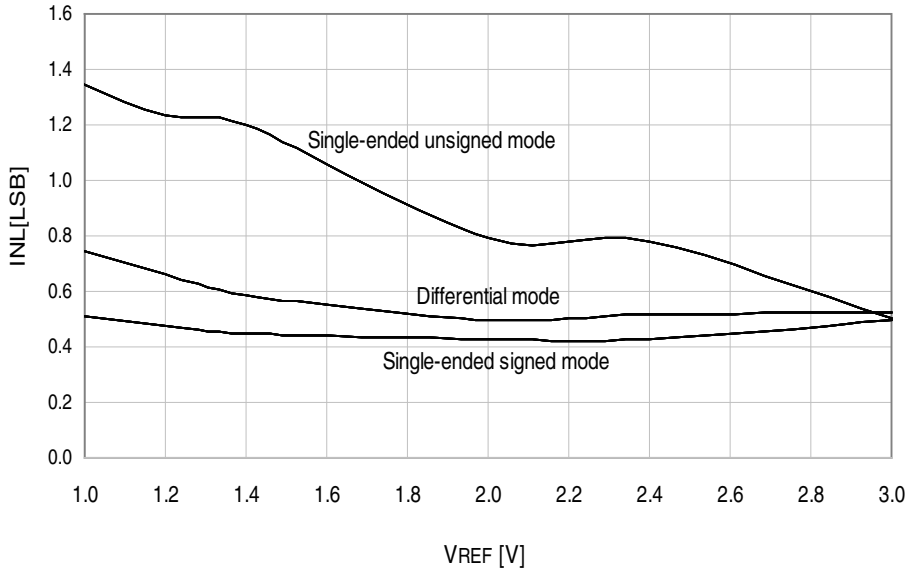
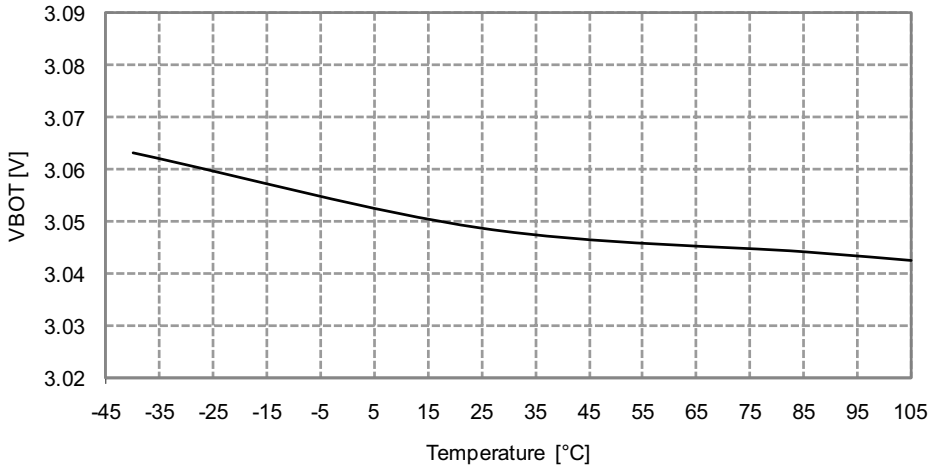


Figure 34-329. BOD Thresholds vs. Temperature

BOD level = 3.0V



34.5.7 External Reset Characteristics

Figure 34-330. Minimum Reset Pin Pulse Width vs. V_{CC}